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IN THE CLAIMS

Please amend claims 25-30 as set forth below.

Claims 1-24 (Canceled)

25. (Currently Amended) A manufacturing method of manufacturing a resin-sealing type semiconductor device, comprising the steps of:

preparing a multi-link lead frame formed by linking in a line with a plurality of package areas in a line, each of the package areas including a plurality of inner leads and, a thin sheet-shaped insulating member joined to an end portion of each of said inner leads and capable of supporting a semiconductor chip;

thereafter mounting a said-semiconductor chip on said insulating member in each of said package areas on which said inner leads and said insulating member are joined;

connecting surface electrodes of said semiconductor chips and said inner leads corresponding thereto by respective a-wires;

forming a seal portion by resin-sealing said semiconductor chips, said wires, and said insulating members; and

separating a plurality of outer leads exposed from said seal portion, from a frame section of said lead frame.

26. (Currently Amended) A manufacturing method of manufacturing a resin-sealing type semiconductor device, comprising the steps of:

preparing a matrix frame formed—by arranging a plurality of package areas in a matrix arrangement, each of the package areas including a plurality of inner leads and, a thin sheet-shaped insulating member joined to an end portion of each of said inner leads and capable of supporting a semiconductor chip;

thereafter mounting a said semiconductor chip on said insulating member in each of said package areas on which said inner leads and said insulating member are joined;

connecting surface electrodes of said semiconductor chips and said inner leads corresponding thereto by $\underline{\text{respective}}$ $\underline{\text{a-wires}}$;

forming a seal portion by resin-sealing said semiconductor chips, said wires, and said insulating members; and

separating a plurality of outer leads exposed from said seal portion, from a frame section of said matrix frame.

27. (Currently Amended) The manufacturing—method of manufacturing a semiconductor device according to claim 25, further comprising—a wherein said mounting is performed by

step of mounting said semiconductor chip on a surface of an inner lead arrangement side of said insulating member—when said semiconductor chip is mounted on said insulating member.

28. (Currently Amended) The manufacturing method of manufacturing a semiconductor device according to claim 25,

wherein said mounting step is performed semiconductor chip is arranged and mounted such that a length of a shorter side of a main surface of said semiconductor chip formed in a an quadrilateral shape is twice or less than twice a distance from a tip of the inner leads arranged at the farthest location from a center line of the semiconductor chip in a plane direction, to said semiconductor chip, when said semiconductor chip is mounted on said insulating member.

29. (Currently Amended) The manufacturing method of manufacturing a semiconductor device according to claim 25, further comprising wherein said preparing step includes a step of being assembled by using said lead frame in which said inner leads and said insulating member are joined by providing an adhesive layer disposed throughout the entirety of a surface of an inner lead arrangement side of said insulating member.

30. (Currently Amended) The manufacturing—method of manufacturing a semiconductor device according to claim 25, further comprising—wherein said preparing step includes a step of being assembled by using said lead frame in which said inner leads and said insulating member are joined by providing an adhesive layer disposed only on a lead joining portion of a surface of an inner lead arrangement side of said insulating member.